

ABSTRACT

A halo implant method for forming halo regions of at least first and second transistors formed on a same semiconductor substrate. The first transistor comprises a first gate region disposed between first and second semiconductor regions. The second transistor comprises a second gate region disposed between third and fourth semiconductor regions. The method comprises the steps of, in turn, halo-implanting each of the first, second, third, and fourth semiconductor regions, with the other three semiconductor regions being masked, in a projected direction which (i) is essentially perpendicular to the direction of the respective gate region and (ii) points from the halo-implanted semiconductor region to the respective gate region.